

## N-Channel Enhancement Mode MOSFET

### 1. Product Information

#### 1.1 Features

- ☒ SGT MOS Technology
- ☒ Low thermal resistance

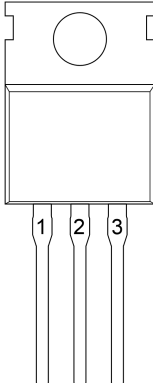
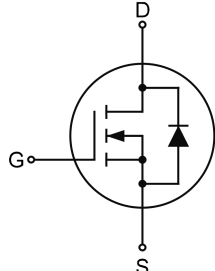
#### 1.2 Applications

- ☒ Battery management
- ☒ Motor control and drive
- ☒ UPS
- ☒ Load switch

#### 1.3 Quick reference

- ☒  $BV \geq 68\text{ V}$
- ☒  $R_{DS(ON)} \leq 6.8\text{ m}\Omega @ V_{GS} = 10\text{ V}$
- ☒  $P_D \leq 150.6\text{ W}$
- ☒  $R_{DS(ON)} \leq 13\text{ m}\Omega @ V_{GS} = 6\text{ V}$
- ☒  $I_D \leq 92\text{ A}$

### 2. Pin Description

| Pin | Description | Simplified Outline                                                                                             | Symbol                                                                                |
|-----|-------------|----------------------------------------------------------------------------------------------------------------|---------------------------------------------------------------------------------------|
| 1   | Gate (G)    |  <p>Top View<br/>TO-220</p> |  |
| 2   | Drain (D)   |                                                                                                                |                                                                                       |
| 3   | Source (S)  |                                                                                                                |                                                                                       |

## 3. Limiting Values

| Symbol          | Parameter                                        | Conditions                                    | Min | Max      | Unit                        |
|-----------------|--------------------------------------------------|-----------------------------------------------|-----|----------|-----------------------------|
| $V_{DS}$        | Drain-Source Voltage                             | $T_C=25^{\circ}\text{C}$                      | 68  | -        | V                           |
| $V_{GS}$        | Gate-Source Voltage                              | $T_C=25^{\circ}\text{C}$                      | -   | $\pm 20$ | V                           |
| $I_D$           | Drain Current (DC)                               | $T_C=25^{\circ}\text{C}$                      | -   | 92       | A                           |
|                 |                                                  | $T_C=100^{\circ}\text{C}, V_{GS}=10\text{ V}$ | -   | 58       | A                           |
| $I_{DM}^*$      | Drain Current (Pulsed)                           | $T_C=25^{\circ}\text{C}, V_{GS}=10\text{ V}$  | -   | 368      | A                           |
| $P_D$           | Drain Power Dissipation                          | $T_C=25^{\circ}\text{C}$                      | -   | 150.6    | W                           |
| $E_{AS}$        | Single Pulsed Avalanche Energy                   | $V_{DD}=30\text{ V}, L=0.3\text{ mH}$         | -   | 140      | mJ                          |
| $I_S$           | Continuous-Source Current                        | $T_C=25^{\circ}\text{C}$                      | -   | 92       | A                           |
| $T_J, T_{stg}$  | Operating Junction and Storage Temperature Range |                                               | -55 | 150      | $^{\circ}\text{C}$          |
| $R_{\theta JA}$ | Thermal Resistance-Junction to Ambient           |                                               | -   | 65       | $^{\circ}\text{C}/\text{W}$ |
| $R_{\theta JC}$ | Thermal Resistance-Junction to Case              |                                               | -   | 0.83     |                             |

Notes:

- \* Pulse width  $\leq 300\text{ }\mu\text{s}$ , duty cycle  $\leq 2\%$ .
- \*\* Surface mounted on 1 in<sup>2</sup> pad area,  $t \leq 10\text{ sec}$ .
- \*\*\* Limited by bonding wire.

## 4. Marking Information

| Product Name | Marking                                                                                                                            |
|--------------|------------------------------------------------------------------------------------------------------------------------------------|
| KJ80N06C     | <div style="border: 1px solid black; padding: 5px; display: inline-block;"> <b>KJ80N06C</b><br/>           XXXXXX-X         </div> |

## 5. Ordering Code

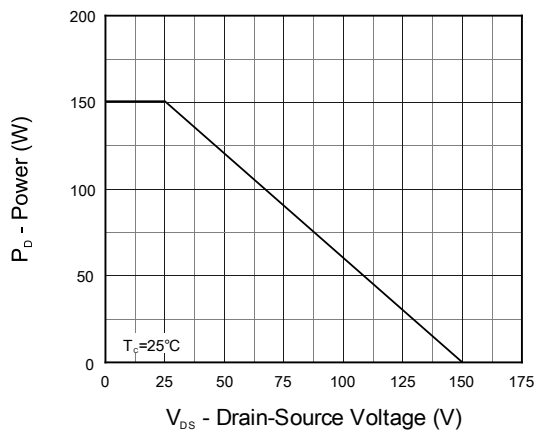
| Product Name | Package | Reel size | Tape width | Quantity (pcs) |
|--------------|---------|-----------|------------|----------------|
| KJ80N06C     | TO-220  | N/A       | N/A        | 1000           |

Note: KJ80N06C defines "Green" as lead-free (RoHS compliant) and halogen free (Br or Cl does not exceed 900 ppm by weight in homogeneous material and total of Br and Cl does not exceed 1500 ppm by weight; Follow IEC 61249-2-21 and IPC/JEDEC J-STD-020C).

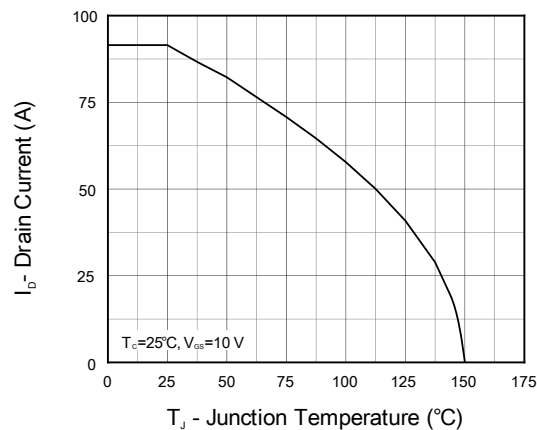
## 6. Electrical Characteristics (T<sub>A</sub>=25°C unless otherwise noted)

| Symbol                      | Parameter                        | Conditions                                                                                | Min | Typ  | Max  | Unit |
|-----------------------------|----------------------------------|-------------------------------------------------------------------------------------------|-----|------|------|------|
| Static Characteristics      |                                  |                                                                                           |     |      |      |      |
| BV <sub>DSS</sub>           | Drain-Source Breakdown Voltage   | V <sub>GS</sub> =0 V, I <sub>DS</sub> =250 μA                                             | 68  | -    | -    | V    |
| V <sub>GS(th)</sub>         | Gate Threshold Voltage           | V <sub>DS</sub> =V <sub>GS</sub> , I <sub>DS</sub> =250 μA                                | 2   | -    | 4    | V    |
| I <sub>DSS</sub>            | Drain Leakage Current            | V <sub>DS</sub> =60 V, V <sub>GS</sub> =0 V                                               | -   | -    | 1    | μA   |
| I <sub>GSS</sub>            | Gate Leakage Current             | V <sub>GS</sub> =±20 V, V <sub>DS</sub> =0 V                                              | -   | -    | ±100 | nA   |
| R <sub>DS(ON)</sub>         | Drain-Source On-State Resistance | V <sub>GS</sub> =10 V, I <sub>DS</sub> =45 A                                              | -   | 5    | 6.8  | mΩ   |
|                             |                                  | V <sub>GS</sub> =6 V, I <sub>DS</sub> =30 A                                               | -   | 11   | 13   | mΩ   |
| R <sub>g</sub>              | Gate resistance                  | V <sub>GS</sub> =0 V, V <sub>DS</sub> =0 V, f=1 MHz                                       | -   | 0.85 | -    | Ω    |
| Diode Characteristics       |                                  |                                                                                           |     |      |      |      |
| V <sub>SD</sub>             | Diode Forward Voltage            | I <sub>SD</sub> =45 A, V <sub>GS</sub> =0 V                                               | -   | -    | 1.3  | V    |
| t <sub>rr</sub>             | Reverse Recovery Time            | I <sub>SD</sub> =45 A, V <sub>DS</sub> =60 V, dI <sub>SD</sub> /dt=100 A/μs               | -   | 40   | -    | ns   |
| Q <sub>rr</sub>             | Reverse Recovery Charge          |                                                                                           | -   | 63   | -    | nC   |
| Dynamic Characteristics     |                                  |                                                                                           |     |      |      |      |
| C <sub>iss</sub>            | Input Capacitance                | V <sub>GS</sub> =0 V, V <sub>DS</sub> =30 V, f=1 MHz                                      | -   | 5400 | -    | pF   |
| C <sub>oss</sub>            | Output Capacitance               |                                                                                           | -   | 285  | -    |      |
| C <sub>rss</sub>            | Reverse Transfer Capacitance     |                                                                                           | -   | 200  | -    |      |
| t <sub>d(on)</sub>          | Turn-on Delay Time               | V <sub>DS</sub> =30 V, V <sub>GEN</sub> =10 V, R <sub>G</sub> =3 Ω, I <sub>DS</sub> =45 A | -   | 21   | -    | ns   |
| t <sub>r</sub>              | Turn-on Rise Time                |                                                                                           | -   | 32   | -    |      |
| t <sub>d(off)</sub>         | Turn-off Delay Time              |                                                                                           | -   | 44   | -    |      |
| t <sub>f</sub>              | Turn-off Fall Time               |                                                                                           | -   | 15   | -    |      |
| Gate Charge Characteristics |                                  |                                                                                           |     |      |      |      |
| Q <sub>g</sub>              | Total Gate Charge                | V <sub>DS</sub> =30 V, V <sub>GS</sub> =10 V, I <sub>DS</sub> =45 A                       | -   | 95   | -    | nC   |
| Q <sub>gs</sub>             | Gate-Source Charge               |                                                                                           | -   | 30   | -    |      |
| Q <sub>gd</sub>             | Gate-Drain Charge                |                                                                                           | -   | 25   | -    |      |

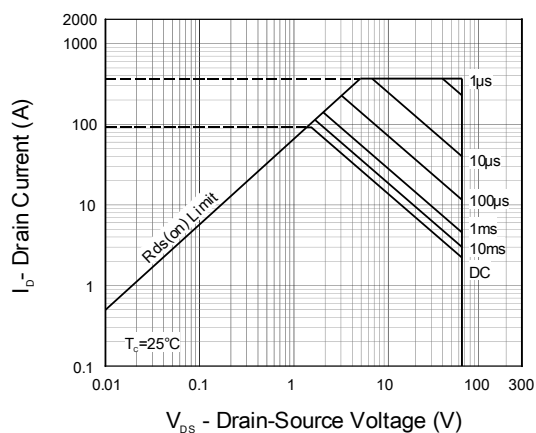
## 7. Typical Characteristics



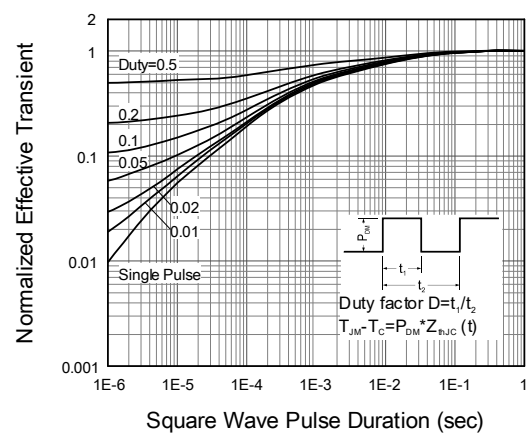
**Figure 1. Output Characteristics**



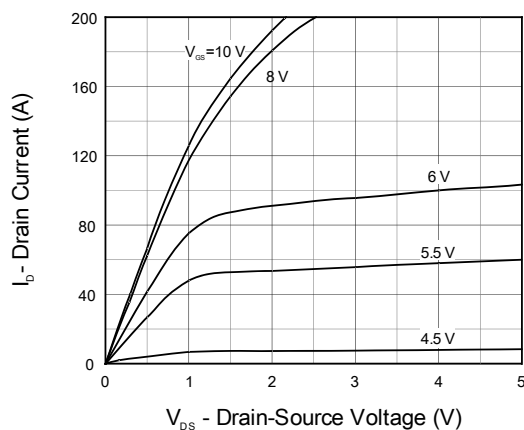
**Figure 2. Current Capability**



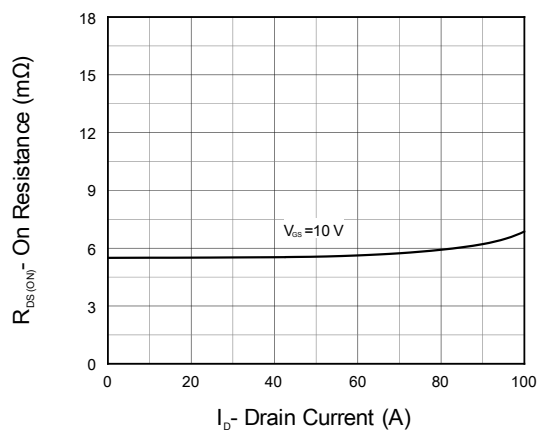
**Figure 3. Safe Operation Area**



**Figure 4. Transient Thermal Impedance**



**Figure 5. Output Characteristics**



**Figure 6. On Resistance**

## 7. Typical Characteristics (cont.)

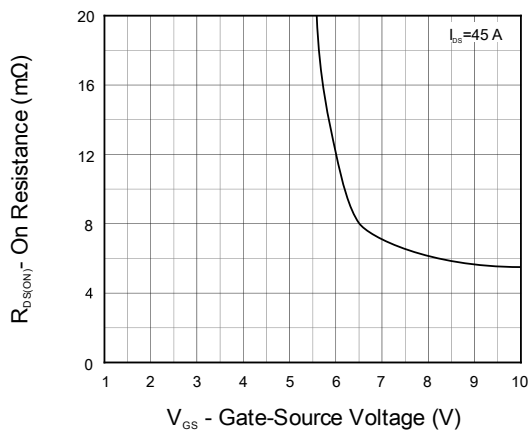


Figure 7. Transfer Characteristics

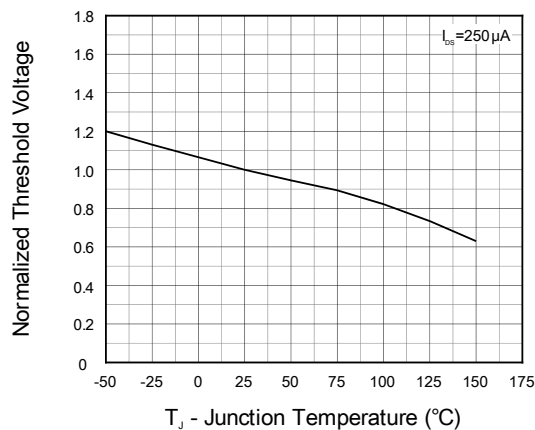


Figure 8. Normalized Threshold Voltage

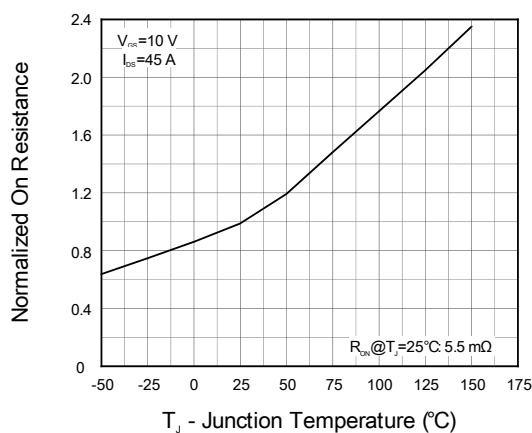


Figure 9. Normalized On Resistance

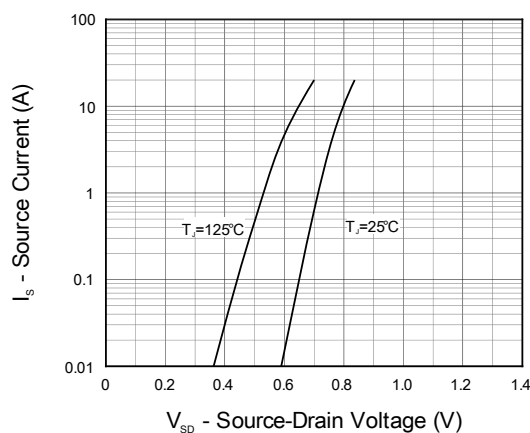


Figure 10. Diode Forward Current

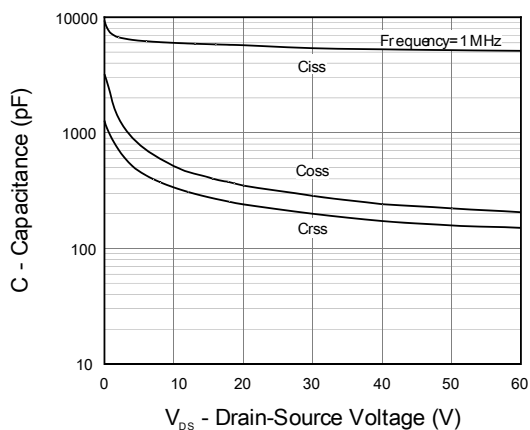


Figure 11. Capacitance

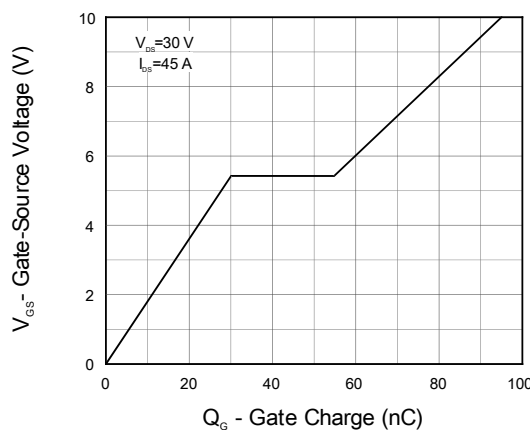
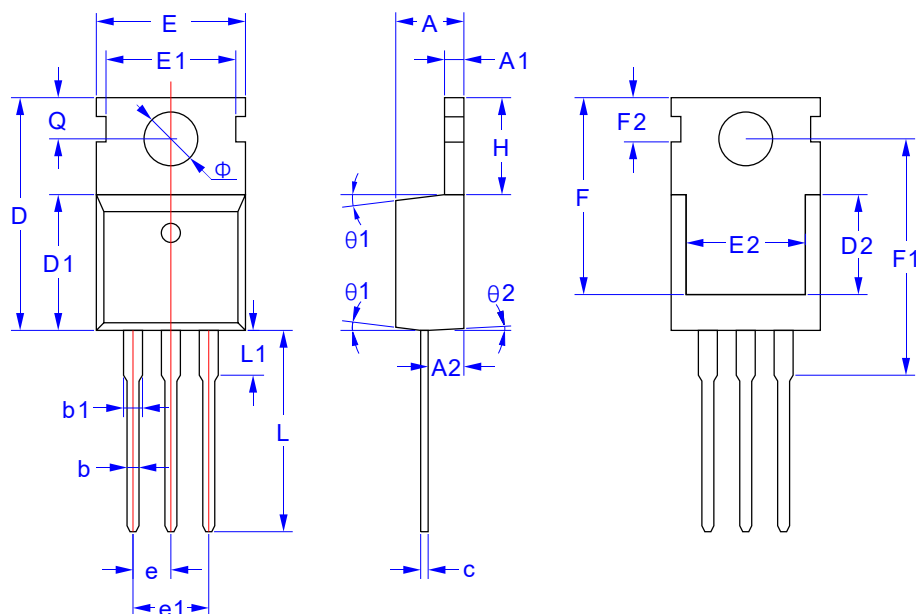


Figure 12. Gate Charge

## 8. Package Dimensions

### TO-220 Package



| Symbol | Dimensions in Millimeters |       |       |
|--------|---------------------------|-------|-------|
|        | MIN                       | NOM   | MAX   |
| A      | 4.27                      | 4.57  | 4.87  |
| A1     | 1.15                      | 1.30  | 1.45  |
| A2     | 2.10                      | 2.40  | 2.70  |
| b      | 0.70                      | 0.80  | 1.00  |
| b1     | 1.17                      | 1.27  | 1.50  |
| c      | 0.40                      | 0.50  | 0.65  |
| D      | 15.50                     | 15.80 | 16.10 |
| D1     | 8.80                      | 9.10  | 9.40  |
| D2     | 5.70                      | 6.70  | 7.00  |
| E      | 9.70                      | 10.00 | 10.30 |
| E1     | -                         | 8.70  | -     |
| E2     | 7.00                      | 8.00  | 8.40  |
| e      | 2.54                      |       |       |
| e1     | 5.08                      |       |       |
| F      | 13.30                     | 13.50 | 13.70 |
| F1     | 15.50                     | 15.90 | 16.30 |
| F2     | 2.80                      | 3.00  | 3.20  |
| H      | 6.00                      | 6.50  | 6.85  |
| L      | 12.75                     | 13.50 | 13.90 |
| L1     | -                         | 3.10  | 3.40  |
| Q      | 2.60                      | 2.80  | 3.00  |
| Φ      | 3.45                      | 3.60  | 3.75  |
| θ1     | 4°                        | 7°    | 10°   |
| θ2     | 0°                        | 3°    | 6°    |